

Inhomogeneous metallic phase upon disordering a two dimensional Mott insulator

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We find that isoelectronic disorder destroys the spectral gap in a Mott-Hubbard insulator in 2D leading, most unexpectedly, to a new metallic phase. This phase is spatially inhomogeneous with metallic behavior coexisting with antiferromagnetic long range order. Even though the Mott gap in the pure system is much larger than antiferromagnetic exchange, the spectral gap is destroyed locally in regions where the disorder potential is high enough to overcome the inter-electron repulsion thereby generating puddles where charge fluctuations are enhanced. With increasing disorder, these puddles expand and concomitantly the states at the Fermi energy get extended leading to a metallic phase. We discuss the implications of our results for experiments.

Disorder can lead to new important phenomena: such as localization in disordered media [1, 2], metal-insulator transitions [3], precisely quantized Hall plateaus in the quantum Hall effect, and zero resistance from pinned vortices in a type II superconductor. In systems as diverse as superconducting InSb [4], high T_c cuprates [5] and manganites [6] disorder produces nanoscale inhomogeneities which can have a profound influence on the properties of these systems.

We propose the existence of a new metallic phase at $T = 0$ which is generated when potential disorder is introduced into a Mott insulator. This metallic phase is highly inhomogeneous and coexists with long range antiferromagnetic order. It is sandwiched between two qualitatively different insulators: at low disorder, a Mott insulator with a spectral gap and antiferromagnetic (AFM) long range order, and, at high disorder, a paramagnetic Anderson insulator with gapless excitations. Our result is surprising since one would expect that the primary role of disorder is to localize wave functions, which is opposite to the conditions for forming extended states necessary for metallic behavior.

We find that the route to the formation of a metal at intermediate disorder is the following: Given a random potential profile, there are two types of regions: weakly disordered (WD) with relatively small potential fluctuations and strongly disordered (SD) with larger fluctuations. AFM order exists in the WD regions that consist of singly occupied sites with a large local Mott gap. On the other hand, in the SD regions the local density deviates from one per site which disrupts the antiferromagnetic ordering and also leads to the collapse of the gap locally. There is thus a 'phase separation' between the insulating AFM WD regions and the metallic SD regions with suppressed AFM. The low lying excitations of the system remain trapped in the SD regions. With increasing disorder the SD regions grow and along with that, the eigenfunctions get extended throughout the system and the system becomes metallic at intermediate disorder. At high disorder the system becomes a paramagnetic Anderson insulator. We substantiate the above picture

with calculations of the magnetic correlations, the local density of states and the optical conductivity.

We propose that experiments on cuprates in their parent Mott insulating phase, could introduce disorder by isoelectronic substitution, or by bombardment, without changing the carrier doping. Such experiments should be able to see this unusual metallic phase at intermediate disorder. Recently, Vajk et. al [7] have measured the spin correlations using neutron scattering in La_2CuO_4 with Zn substitution on the Cu sites. It will be necessary to complement the magnetic information from neutron scattering with transport and spectroscopy to look for signatures of an inhomogeneous metallic phase.

Model and Calculation: We model the 2D disordered Mott insulator by a repulsive Hubbard model at half filling (one electron per site) with potential disorder:

$$H = K + U \sum_i n_i \uparrow n_i \downarrow + \sum_{i,j} (V_i - V_j) n_i : \quad (1)$$

$K = t \sum_{\langle ij \rangle} (c_i^\dagger c_j + \text{h.c.})$ is the kinetic energy, c_i^\dagger (c_i) the creation (destruction) operator for an electron with spin σ on a site r_i of a square lattice of N sites, t the near-neighbor hopping, U is the on-site repulsion between electrons, $n_i = c_i^\dagger c_i$, and μ the chemical potential. The random potential V_i is chosen independently at each r_i and is uniformly distributed in the interval $[-V; V]$; V thus controls the strength of the disorder. All energies are measured in units of t . This is a minimal model containing the interplay of electronic correlations and localization: for zero disorder $V = 0$ it describes a Mott insulator at half filling, and for $U = 0$ it reduces to the (non-interacting) Anderson localization problem. We report results for $U = 4t$ and lattices up to 50×50 .

The dynamical mean field theory [8] has been widely used to study Mott insulators and includes the quantum fluctuations associated with an effectively single site approximation of the system. The inhomogeneous Hartree Fock approximation that we implement here is a complementary method which does not contain the dynamical fluctuations but, when solved self consistently as we do

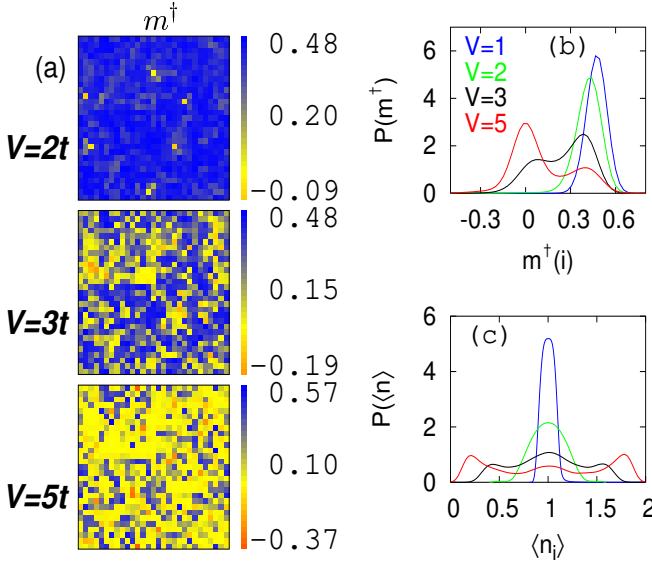


FIG. 1: (a) Left panels show the local staggered magnetization $m^y(i) = \langle S_z(i) - S_z(i+1) \rangle$. The regions in blue have AFM order; the defective sites with reduced AFM order are shown in yellow and red. The data is for the disordered Hubbard model at half filling with $U = 4t$ on a 28×28 lattice for disorder strengths $V = 2t$; $V = 3t$; $V = 5t$ for one realization of disorder. (b) Probability distribution $P(m^y)$ of $m^y(i)$ for different values of V . For $V = 1$, $P(m^y)$ has a peak near 0.4. With increasing V , $P(m^y)$ gets broader and develops weight near 0 indicating the growth of paramagnetic regions. (c) Probability distribution $P(n)$ of the site-occupancy n_i for different values of V . For $V = 1$, $P(n)$ has a peak near an average single site occupancy $\langle n_i \rangle = 1$. With increasing V , $P(n)$ gets broader and develops weight for doubly occupied and unoccupied sites.

here, captures the inhomogeneity in the spatial structure of the electronic density, a feature which is at the heart of problems with disorder. The only known way to include both the spatial and temporal fluctuations is quantum Monte Carlo (QMC) but that method too has limitations arising from finite size effects, inability to extract dynamical information without the use of complicated maximum entropy methods and the sign problem for fermions that limits the calculations to finite temperatures. We begin by treating the spatial fluctuations of the local densities $n_i = \langle c_{i\uparrow}^\dagger c_{i\uparrow} \rangle$ and local magnetic fields $h_i = U \langle c_{i\uparrow}^\dagger c_{i\uparrow} \rangle$ and $h_i = U \langle c_{i\downarrow}^\dagger c_{i\downarrow} \rangle$ using a site dependent mean field approximation. As a consequence, we get an effective Hamiltonian which is quadratic in the fermion operators and can be diagonalized for a system with periodic boundary conditions. Starting with an initial guess for h_i 's and n_i 's [9] we numerically solve for the eigenvalues ϵ_n and eigenvectors $\phi_n(r_i)$ of a $2N \times 2N$ matrix. The local fields are then determined in terms of the eigenfunctions and the eigenvalue problem with these new local fields as input is then iterated until self-consis-

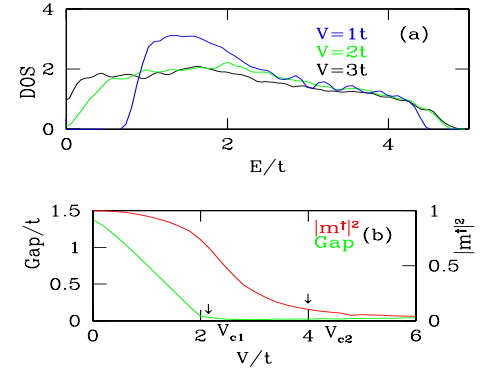


FIG. 2: (a) Density of states averaged over 10 realizations at half filling and $U = 4t$ for $V=t = 1; 2; 3$. For $V = t$ there is a Mott gap in the spectrum at the chemical potential $E = 0$; and for $V = 2t$ the gap has closed. (b) Single particle energy gap as a function of V showing the collapse of the gap at $V_{c1} = 2.2t$ (scale on LHS). The decrease of the AFM staggered order parameter m^y (scale on RHS), as a function of disorder strength V and its vanishing beyond $V_{c2} = 4t > V_{c1}$. Note that at $V = 2t$ the system is still strongly AFM even though the Mott gap has vanished.

tency is achieved at each site.

Antiferromagnetic Order and Spectral Gap: Fig. 1 shows that the local staggered magnetization $m^y(i) = \langle S_z(i) - S_z(i+1) \rangle$ is largely antiferromagnetic for $V = 2t$ with a few local defective regions. With increasing disorder the defective regions having reduced antiferromagnetic order grow in size.

We next look at the behavior of the two defining characteristics of a Mott insulator in Fig. 2: the spectral gap obtained from the lowest eigenvalue of the effective Hamiltonian, and the AFM order parameter $m^y(i)$ obtained from the spatial behavior of the spin-spin correlation function at large distances, as a function of disorder. The first surprise is that even though the energy scale for charge fluctuations is $U - J^2/U = U$, the scale for antiferromagnetic exchange, the spectral gap vanishes at $V_{c1} = 2.2t$ which is lower than the critical disorder $V_{c2} = 4t$ where AFM long range order (AFLRO) vanishes.

The occurrence of two critical disorder strengths defines three distinct regions: In region I defined by $0 < V < V_{c1}$ the system is a Mott insulator with a finite gap and AFLRO. The intermediate region II, $V_{c1} < V < V_{c2}$ is extremely unusual with AFLRO but no gap and is discussed in greater detail below. In region III, $V > V_{c2}$ the system is simply an Anderson or localized insulator with gapless excitations and no magnetic order.

Nature of eigenfunctions: We argue below that in region II the system is a disordered AFM metal. How does this metal come about? The spatial extent of the eigenstates near the Fermi energy in Fig. 3(a) dis-

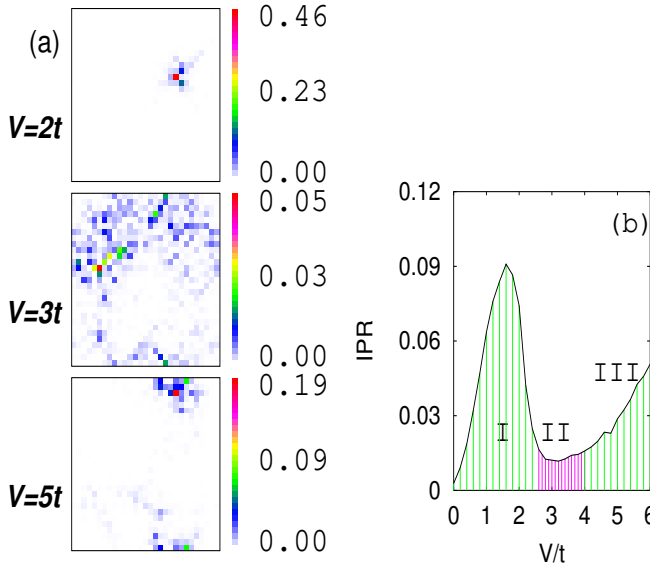


FIG. 3: (a) Single particle eigenstates at the Fermi energy for disorder strengths $V = 2t, 3t, 5t$. Note that the eigenstates are localized for low $V = 2t$ and high disorder $V = 5t$ but surprisingly are more extended at intermediate disorder of $V = 3t$. (b) Inverse participation ratio (IPR) or the localization length ℓ_{loc} for the wave function at the Fermi energy as a function of disorder V . In both regions I and III IPR increases with disorder or ℓ_{loc} decreases with disorder, as expected. But in the intermediate region II, the wave function in fact gets less localized with increasing disorder.

tinctly shows that they are localized at low $V = 2t$ and high disorder $V = 5t$, but quite surprisingly at intermediate disorder $V = 3t$ the states get more extended. The localization length $\ell_{\text{loc}}(\omega)$ for the (normalized) state $\psi(\mathbf{r}_i)$ is related to the inverse participation ratio $\text{IPR} = \sum_i |\psi(\mathbf{r}_i)|^4 / \sum_i |\psi(\mathbf{r}_i)|^2$ [2]. One would expect that with increasing disorder, ℓ_{loc} would decrease or correspondingly IPR would increase. Instead we see in Fig. 3(b) a very definite decrease in IPR for $V = 2$ signaling that even though disorder is increasing the states are getting more extended. Such anomalous behavior continues till about $V = 3U=4$ and then once again reverts to the usual behavior where IPR increases with V . Based on numerical calculations on finite size systems it is difficult to prove if the states in region II are truly extended, but what is abundantly clear is that the IPR does show a very definite non-monotonic behavior signaling a marked change in the nature of the states, at least on mesoscopic scales.[10].

Previous QMC simulations on disordered bosonic[11] and fermionic[12] have shown that potential disorder that breaks particle-hole symmetry produces superfluidity – ness or conductivity which can increase with disorder. At a Hartree Fock level such an effect can be understood as a screening of the random potential by the interactions

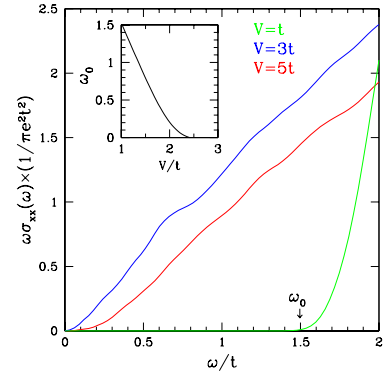


FIG. 4: Frequency dependence of the conductivity for $V = 1t$ in region I showing a gap Δ_0 in the joint density of states; for $V = 3t$ in region II showing a linear dependence indicative of metallic behavior; and for $V = 5t$ in region III showing ω^3 dependence indicative of Anderson localization. The inset shows the decrease of the gap Δ_0 with increasing disorder V and its vanishing around $V_{c1} = 2.2t$.

between the particles[15]. Our calculations go beyond simple screening arguments and have revealed the physical origin of the anomalous behavior seen in Fig. 3 at a microscopic level.

Frequency-dependent conductivity: The nature of the frequency dependent conductivity $\text{Re}(\sigma(\omega)) = \text{Im}(\sigma(\omega)) = \sigma(\omega)$ gives insight into the conducting properties of the phases.

$\sigma(\omega)$ is the Fourier transform of $\langle j(t)j(0) \rangle$, the (disorder averaged) current-current correlation function. As shown in Fig. 4 the low frequency behavior of $\sigma(\omega)$ has a finite gap in the Mott region I for $V = t$; shows a linear ω dependence in the metallic region II for $V = 3t$ which implies that there is a finite dc conductivity $\sigma(0)$; and shows a ω^3 dependence in the Anderson insulating regime III for $V = 5t$, which implies that there are gapless excitations but nevertheless $\sigma(0) = 0$.

Origin of the Metallic Phase: Now that we have seen evidence for a metallic phase at intermediate disorder, the question arises as to how such a phase comes about.

In the clean system, the repulsive interactions prevent double occupancy. But once there is potential disorder, electrons can hop into sites that have deep potential wells and thereby lower their energy. This leads to a broadened distribution of local occupancy and a growth of paramagnetic sites, as illustrated in Fig. 1. In the classical limit, sites with a large positive potential $V_i > U=2$ are unoccupied; sites with $-U=2 < V_i < U=2$ are singly occupied; and sites with large negative $V_i < -U=2$ are doubly occupied. Only sites with one electron can contribute to AFM order if they form a connected cluster. The critical probability p_c for classical percolation of vacancies on a 2D square lattice is $p_c = 0.41$ which should equal the density of doubly and unoccupied sites, so that $p_c = 1 - U/(2V)$ which implies that $(V=U)_c = 1/2(1 - p_c) = 0.35$. This

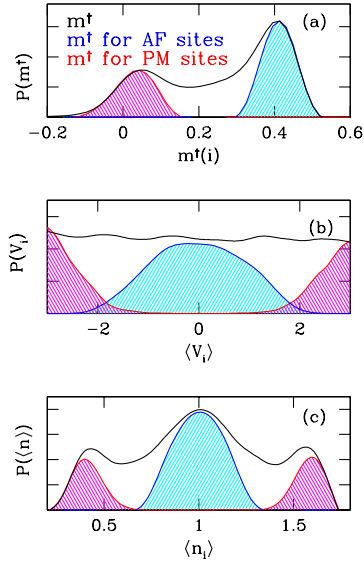


FIG. 5: (a) Histogram $P(m^y)$ of the local staggered magnetization (black). We will define those sites with staggered magnetization 0.38 and more to be AFM sites (region shown in blue); and sites with $hS_z(i)$ in the range $(-0.1, 0.1)$ to be paramagnetic PM sites (shown in red). (b) Histogram $P(V)$ of the local disorder potential for all sites (black); histogram of AFM sites (blue) which coincide with the less disordered WD regions; and histogram of PM sites (red) in the SD regions. (c) Histogram $P(n)$ of the local density for all sites (black); for AFM sites (blue); and for PM sites (red).

indicates that an estimate of $V_{c2} \approx 3.4t$ for $U = 4t$. We have compared our results for m^y as a function of V with the percolation of vacancies in a quantum Heisenberg model and find very good agreement [3, 14].

Fig. 5, which shows the correlation between the strength of disorder and the nature of the regions, is very revealing. It clearly shows a reorganization or a phase separation of the system into WD regions that are AFM and have a local density of one electron per site, and the SD regions which are PM with a bimodal density clustering towards zero and two per site. Our results for the existence of metallic behavior in 2D is even more surprising when we recall the scaling theory of localization for non-interacting electrons [1] which claims that in dimensions less than and equal to two all the single particle states are localized by arbitrarily small amounts of disorder. Thus the underlying picture that emerges for the origin of the unusual metal at intermediate disorder in a Mott insulator at half filling is a percolation of the defected SD regions with reduced AFM. As seen in Fig. 3(a) (top panel) the lowest excitations live in these defected SD regions and with increasing disorder the defective regions expand and along with that the excitations get more delocalized as they are able to travel on the ex-

panding SD clusters, see Fig. 3(a) (middle panel). This is a rather remarkable situation that increasing disorder in a correlated system is able to induce metallic behavior. With further increase of disorder the states on the percolating cluster get localized and the system becomes an Anderson insulator, see Fig. 3(a) (bottom panel).

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